


MAC218A6FP, MAC218A8FP MAC218A10FP

Preferred Devices


Triacs

Silicon Bidirectional Thyristors

Designed primarily for full-wave ac control applications, such as light dimmers, motor controls, heating controls and power supplies.

- Blocking Voltage to 800 Volts
- Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Isolated TO-220 Type Package for Ease of Mounting
- Gate Triggering Guaranteed in Four Modes
-  Indicates UL Registered – File #E69369
- Device Marking: Logo, Device Type, e.g., MAC218A6FP, Date Code

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)


Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1.) ($T_J = -40$ to $+125^\circ\text{C}$, Sine Wave 50 to 60 Hz, Gate Open) MAC218A6FP MAC218A8FP MAC218A10FP	V_{DRM} , V_{RRM}	400 600 800	Volts
On-State RMS Current ($T_C = +80^\circ\text{C}$) (Note 2.) Full Cycle Sine Wave 50 to 60 Hz	$I_{\text{T(RMS)}}$	8.0	Amps
Peak Non-Repetitive Surge Current (One Full Cycle, 60 Hz, $T_C = +80^\circ\text{C}$) Preceded and followed by rated current	I_{TSM}	100	Amps
Circuit Fusing Considerations ($t = 8.3$ ms)	I^2t	40	A^2s
Peak Gate Power ($T_C = +80^\circ\text{C}$, Pulse Width = 10 μs)	P_{GM}	16	Watts
Average Gate Power ($T_C = +80^\circ\text{C}$, $t = 8.3$ ms)	$P_{\text{G(AV)}}$	0.35	Watt
Peak Gate Current ($T_C = +80^\circ\text{C}$, Pulse Width = 10 μs)	I_{GM}	4.0	Amps
RMS Isolation Voltage ($T_A = 25^\circ\text{C}$, Relative Humidity $\leq 20\%$) 	$V_{\text{(ISO)}}$	1500	Volts
Operating Junction Temperature	T_J	-40 to $+125$	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to $+150$	$^\circ\text{C}$

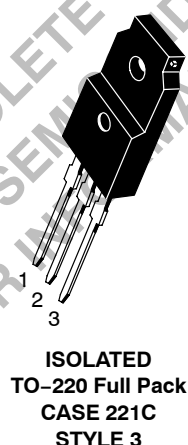
1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.
2. The case temperature reference point for all T_C measurements is a point on the center lead of the package as close as possible to the plastic body.



ON SemiconductorTM

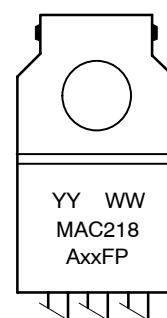
<http://onsemi.com>

ISOLATED TRIAC 
8 AMPERES RMS
400 thru 800 VOLTS



**ISOLATED
TO-220 Full Pack
CASE 221C
STYLE 3**

MARKING DIAGRAM



MAC218AxxFP = Specific Device Code
xx = 6, 8 or 10
YY = Year
WW = Work Week

PIN ASSIGNMENT

	PIN ASSIGNMENT
1	Main Terminal 1
2	Main Terminal 2
3	Gate

ORDERING INFORMATION

Device	Package	Shipping
MAC218A6FP	ISOLATED TO220FP	500/Box
MAC218A8FP	ISOLATED TO220FP	500/Box
MAC218A10FP	ISOLATED TO220FP	500/Box

Preferred devices are recommended choices for future use and best overall value.

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THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.2	°C/W
Thermal Resistance, Case to Sink	$R_{\theta CS}$	2.2 (typ)	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T_L	260	°C

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Peak Repetitive Blocking Current ($V_D = \text{Rated } V_{DRM}$, V_{RRM} : Gate Open)	I_{DRM} , I_{RRM}	–	–	10	μA
$T_J = 125^\circ\text{C}$		–	–	2.0	mA

ON CHARACTERISTICS

Peak On-State Voltage (Note 1) ($I_{TM} = \pm 11.3 \text{ A Peak}$)	V_{TM}	–	1.7	2.0	Volts
Gate Trigger Current (Continuous dc) ($V_D = 12 \text{ Vdc}$, $R_L = 100 \Omega$) MT2(+), G(+) MT2(+), G(–) MT2(–), G(–) MT2(–), G(+)	I_{GT}	– – – –	– – – –	50 50 50 75	mA
Gate Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 Vdc, $R_L = 100 \text{ Ohms}$) MT2(+), G(+) MT2(+), G(–) MT2(–), G(–) MT2(–), G(+)	V_{GT}	– – – –	0.9 0.9 1.1 1.4	2.0 2.0 2.0 2.5	Volts
Gate Non-Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 V, $R_L = 100 \Omega$, $T_J = +125^\circ\text{C}$) All Four Quadrants	V_{GD}	0.2	–	–	Volts
Holding Current ($V_D = 12 \text{ Vdc}$, Gate Open, Initiating Current = $\pm 200 \text{ mA}$)	I_H	–	–	50	mA

DYNAMIC CHARACTERISTICS

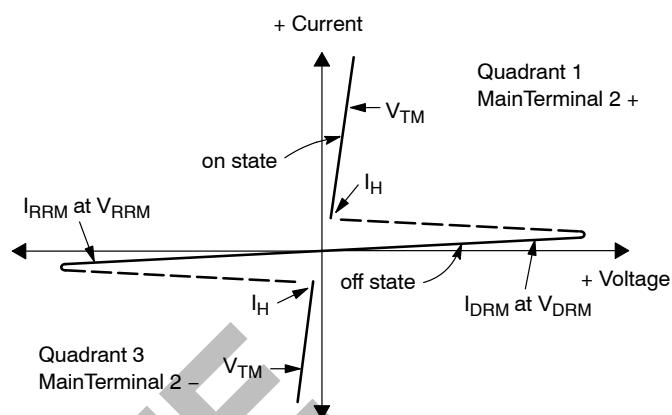
Critical Rate of Rise of Commutating Off-State Voltage ($V_D = \text{Rated } V_{DRM}$, $I_{TM} = 11.3 \text{ A}$, Commutating $di/dt = 4.1 \text{ A/ms}$, Gate Unenergized, $T_C = 80^\circ\text{C}$)	$dv/dt_{(c)}$	–	5.0	–	$\text{V}/\mu\text{s}$
Critical Rate of Rise of Off-State Voltage ($V_D = \text{Rated } V_{DRM}$, Exponential Voltage Rise, Gate Open, $T_J = 125^\circ\text{C}$)	dv/dt	–	100	–	$\text{V}/\mu\text{s}$

1. Pulse Test: Pulse Width $\leq 2.0 \text{ ms}$, Duty Cycle $\leq 2\%$.

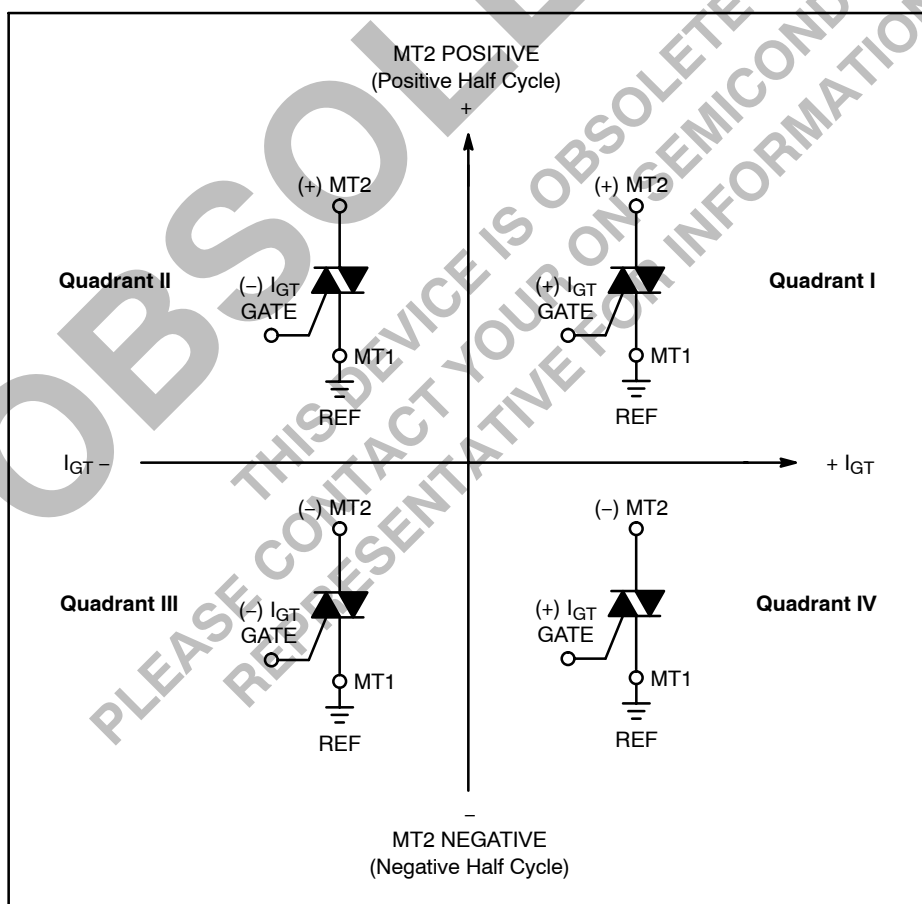
MAC218A6FP, MAC218A8FP MAC218A10FP

Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I_H	Holding Current



Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

MAC218A6FP, MAC218A8FP MAC218A10FP

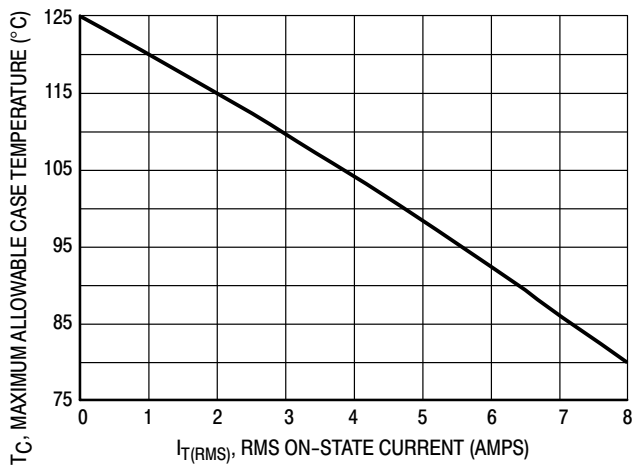


Figure 1. Current Derating

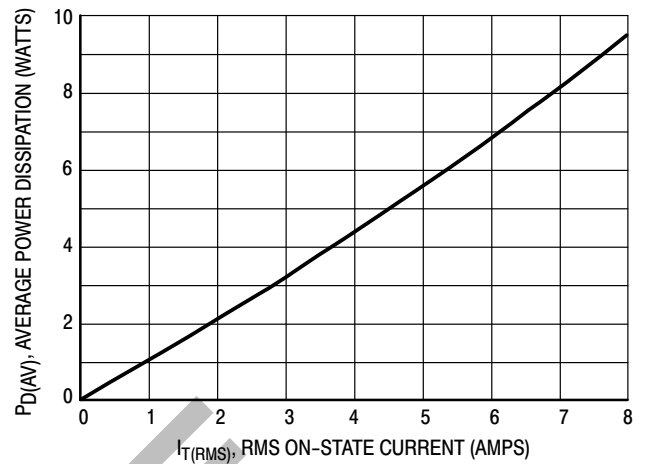


Figure 2. Power Dissipation

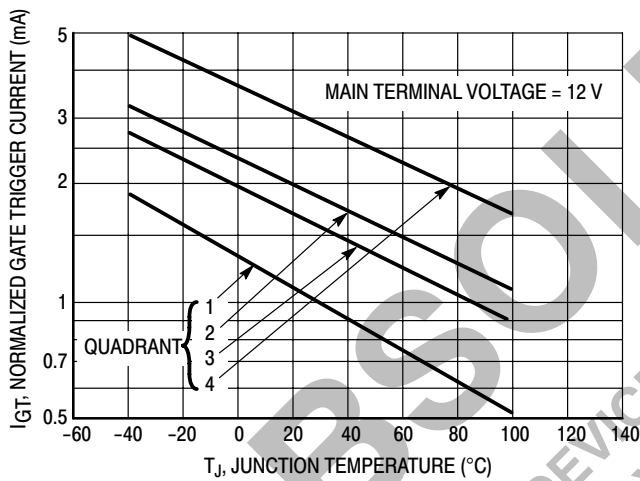


Figure 3. Normalized Gate Trigger Current

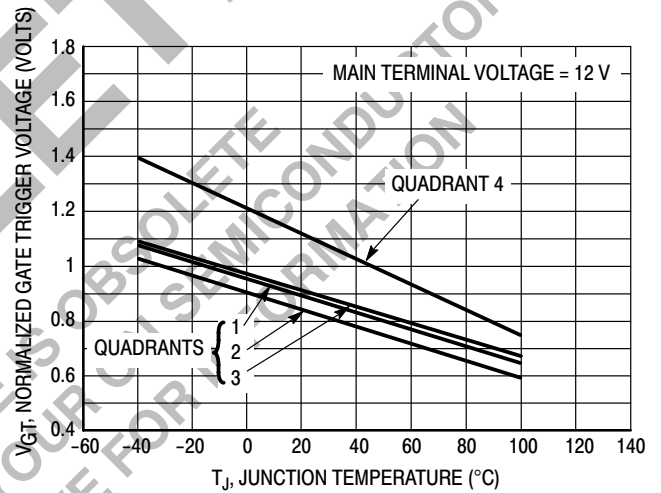


Figure 4. Normalized Gate Trigger Voltage

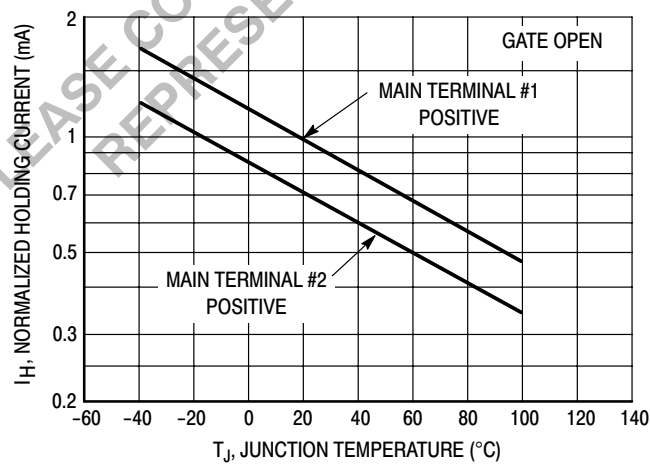


Figure 5. Normalized Holding Current

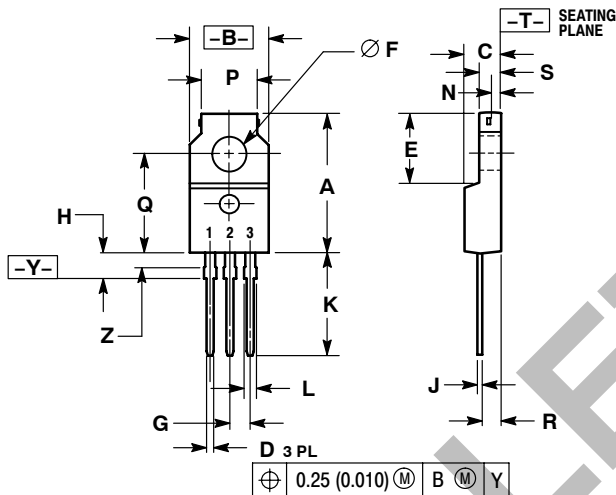
MAC218A6FP, MAC218A8FP MAC218A10FP

PACKAGE DIMENSIONS

TO-220 FULLPACK THYRISTOR

CASE 221C-02

ISSUE D



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. LEAD DIMENSIONS UNCONTROLLED WITHIN DIMENSION Z.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.680	0.700	17.28	17.78
B	0.388	0.408	9.86	10.36
C	0.175	0.195	4.45	4.95
D	0.025	0.040	0.64	1.01
E	0.340	0.355	8.64	9.01
F	0.140	0.150	3.56	3.81
G	0.100 BSC		2.54 BSC	
H	0.110	0.155	2.80	3.93
J	0.018	0.028	0.46	0.71
K	0.500	0.550	12.70	13.97
L	0.045	0.070	1.15	1.77
N	0.049	---	1.25	---
P	0.270	0.290	6.86	7.36
Q	0.480	0.500	12.20	12.70
R	0.090	0.120	2.29	3.04
S	0.105	0.115	2.67	2.92
Z	0.070	0.090	1.78	2.28

STYLE 3:

- PIN 1. MT 1
- MT 2
- GATE

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